

18 V, Precision, Micropower CMOS RRIO Operational Amplifier

AD8657

FEATURES

Micropower at high voltage (18 V): 18 μ A typical

Low offset voltage: $350 \mu V$ maximum Single-supply operation: 2.7 V to 18 VDual-supply operation: $\pm 1.35 V$ to $\pm 9 V$

Low input bias current: 20 pA Gain bandwidth: 200 kHz

Unity-gain stable

Excellent electromagnetic interference immunity

APPLICATIONS

Portable operating systems
Current monitors
4 mA to 20 mA loop drivers
Buffer/level shifting
Multipole filters
Remote/wireless sensors
Low power transimpedance amplifiers

GENERAL DESCRIPTION

The AD8657 is a dual, precision, micropower, rail-to-rail input/output (RRIO) amplifier optimized for low power and wide operating supply voltage range applications.

The AD8657 operates from 2.7 V up to 18 V with a typical quiescent supply current of 18 μ A. It uses the Analog Devices, Inc., patented DigiTrim* trimming technique, which achieves low offset voltage. The AD8657 also has high immunity to electromagnetic interference.

The combination of low supply current, low offset voltage, very low input bias current, wide supply range, and rail-to-rail input and output makes the AD8657 ideal for current monitoring and current loops in process and motor control applications. The combination of precision specifications makes this device ideal for dc gain and buffering of sensor front ends or high impedance input sources in wireless or remote sensors or transmitters.

The AD8657 is specified over the extended industrial temperature range (-40° C to $+125^{\circ}$ C) and is available in an 8-lead MSOP package.

PIN CONFIGURATION



Figure 1.8-Lead MSOP

Table 1. Micropower Op Amps

Table 1. Micropower Op Amps							
Supply Voltage	5 V	12 V to 16 V	36 V				
Single	AD8500	AD8663					
	ADA4505-1						
	AD8505						
	AD8541						
	AD8603						
Dual	AD8502	AD8667	OP295				
	ADA4505-2	OP281	ADA4062-2				
	AD8506						
	AD8542						
	AD8607						
Quad	AD8504	AD8669	OP495				
	ADA4505-4	OP481	ADA4062-4				
	AD8508						
	AD8544						
	AD8609						

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REVISION HISTORY

1/11—Revision 0: Initial Version

SPECIFICATIONS

ELECTRICAL CHARACTERISTICS—2.7 V OPERATION

 $\rm V_{SY}$ = 2.7 V, $\rm V_{CM}$ = V $_{SY}/2$, $\rm T_A$ = 25 °C, unless otherwise specified.

Table 2.

Parameter	Symbol	Test Conditions/Comments	Min	Тур	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{os}	$V_{CM} = 0 \text{ V to } 2.7 \text{ V}$			350	μV
		$V_{CM} = 0.3 \text{ V to } 2.4 \text{ V}; -40^{\circ}\text{C} \le T_{A} \le +85^{\circ}\text{C}$			1	mV
		$V_{CM} = 0 \text{ V to } 2.7 \text{ V}; -40^{\circ}\text{C} \le T_{A} \le +85^{\circ}\text{C}$			2.2	mV
		$V_{CM} = 0.3 \text{ V to } 2.4 \text{ V}; -40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$			2.5	mV
		$V_{CM} = 0 \text{ V to } 2.7 \text{ V}; -40^{\circ}\text{C} \le T_A \le +125^{\circ}\text{C}$			4	mV
Input Bias Current	I _B			1	10	pA
		$-40^{\circ}\text{C} \le \text{T}_{A} \le +125^{\circ}\text{C}$			2.6	nA
Input Offset Current	Ios				20	pА
		$-40^{\circ}\text{C} \le \text{T}_{A} \le +125^{\circ}\text{C}$			500	pА
Input Voltage Range			0		2.7	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = 0 \text{ V to } 2.7 \text{ V}$	79	95		dB
		$V_{CM} = 0.3 \text{ V to } 2.4 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +85^{\circ}\text{C}$	70			dB
		$V_{CM} = 0 \text{ V to } 2.7 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +85^{\circ}\text{C}$	64			dB
		$V_{CM} = 0.3 \text{ V to } 2.4 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$	63			dB
		$V_{CM} = 0 \text{ V to } 2.7 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$	60			dB
Large Signal Voltage Gain	A_{VO}	$R_L = 100 \text{ k}\Omega, V_O = 0.5 \text{ V to } 2.2 \text{ V}$	94	105		dB
		$-40^{\circ}\text{C} \le \text{T}_{A} \le +85^{\circ}\text{C}$	75			dB
		$-40^{\circ}\text{C} \le \text{T}_{A} \le +125^{\circ}\text{C}$	65			dB
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$			2		μV/°C
Input Resistance	R _{IN}			10		GΩ
Input Capacitance, Differential Mode	C_{INDM}			3.5		pF
Input Capacitance, Common Mode	C _{INCM}			3.5		pF
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$R_L = 100 \text{ k}\Omega \text{ to V}_{CM'} - 40^{\circ}\text{C} \le T_A \le +125^{\circ}\text{C}$	2.69			V
Output Voltage Low	V_{OL}	$R_L = 100 \text{ k}\Omega \text{ to V}_{CM'} - 40^{\circ}\text{C} \le T_A \le +125^{\circ}\text{C}$			10	mV
Short-Circuit Current	I _{sc}			±4		mA
Closed-Loop Output Impedance	Z _{OUT}	$f = 1 \text{ kHz}, A_V = 1$		20		Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_{SY} = 2.7 \text{ V to } 18 \text{ V}$	105	125		dB
		$-40^{\circ}\text{C} \le \text{T}_{A} \le +125^{\circ}\text{C}$	70			dB
Supply Current per Amplifier	I _{SY}	$I_0 = 0 \text{ mA}$		18	22	μΑ
		$-40^{\circ}\text{C} \le \text{T}_{A} \le +125^{\circ}\text{C}$			33	μΑ
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 1 \text{ M}\Omega, C_L = 10 \text{ pF, } A_V = 1$		38		V/ms
Settling Time to 0.1%	t _s	$V_{IN} = 1 \text{ V step, } R_{L} = 100 \text{ k}\Omega, C_{L} = 10 \text{ pF}$		14		μs
Gain Bandwidth Product	GBP	$R_L = 1 M\Omega, C_L = 10 pF, A_V = 1$		170		kHz
Phase Margin	Φ_{M}	$R_L = 1 M\Omega, C_L = 10 pF, A_V = 1$		69		Degrees
Channel Separation	CS	$f = 10 \text{ kHz}, R_L = 1 \text{ M}\Omega$		105		dB
EMI Rejection Ratio of +IN x	EMIRR	V _{IN} = 100 mV _{PEAK} , f = 400 MHz, 900 MHz, 1800 MHz, 2400 MHz		90		dB
NOISE PERFORMANCE						
Voltage Noise	e _n p-p	f = 0.1 Hz to 10 Hz		6		μV p-p
Voltage Noise Density	e _n	f = 1 kHz		60		nV/√Hz
		f = 10 kHz		56		nV/√Hz
Current Noise Density	i _n	f = 1 kHz		0.1		pA/√Hz

ELECTRICAL CHARACTERISTICS—10 V OPERATION

 $V_{SY} = 10$ V, $V_{CM} = V_{SY}/2$, $T_A = 25$ °C, unless otherwise specified.

Table 3.

Parameter	Symbol	Test Conditions/Comments	Min	Тур	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V _{os}	$V_{CM} = 0 \text{ V to } 10 \text{ V}$			350	μV
		$V_{CM} = 0 \text{ V to } 10 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +85^{\circ}\text{C}$			2.7	mV
		$V_{CM} = 0 \text{ V to } 10 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$			9	mV
Input Bias Current	I _B			2	15	pA
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$			2.6	nA
Input Offset Current	I _{os}				30	pA
		-40 °C \leq T _A \leq $+125$ °C			500	рА
Input Voltage Range			0		10	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = 0 \text{ V to } 10 \text{ V}$	90	105		dB
		$V_{CM} = 0 \text{ V to } 10 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +85^{\circ}\text{C}$	72			dB
		$V_{CM} = 0 \text{ V to } 10 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$	64			dB
Large Signal Voltage Gain	A _{VO}	$R_1 = 100 \text{ k}\Omega$, $V_0 = 0.5 \text{ V to } 9.5 \text{ V}$	105	120		dB
		-40 °C $\leq T_A \leq +85$ °C	95			dB
		-40°C ≤ T _A ≤ +125°C	67			dB
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$			2		μV/°C
Input Resistance	R _{IN}			10		GΩ
Input Capacitance, Differential Mode	C _{INDM}			3.5		pF
Input Capacitance, Common Mode	C _{INCM}			3.5		pF
OUTPUT CHARACTERISTICS	iiveivi					
Output Voltage High	V_{OH}	$R_L = 100 \text{ k}\Omega \text{ to V}_{CM}, -40^{\circ}\text{C} \le T_A \le +125^{\circ}\text{C}$	9.98			V
Output Voltage Low	V _{OL}	$R_L = 100 \text{ k}\Omega \text{ to V}_{CM'} - 40^{\circ}\text{C} \le T_A \le +125^{\circ}\text{C}$			20	mV
Short-Circuit Current	I _{sc}	L 11 CIVIP 1 A		±11		mA
Closed-Loop Output Impedance	Z _{OUT}	$f = 1 \text{ kHz, } A_v = 1$		15		Ω
POWER SUPPLY	001	, ,				
Power Supply Rejection Ratio	PSRR	$V_{SY} = 2.7 \text{ V to } 18 \text{ V}$	105	125		dB
		$-40^{\circ}\text{C} \le \text{T}_{A} \le +125^{\circ}\text{C}$	70			dB
Supply Current per Amplifier	I _{SY}	$I_0 = 0 \text{ mA}$		18	22	μΑ
ospp.y camerope a map more	-51	-40°C ≤ T _A ≤ +125°C			33	μΑ
DYNAMIC PERFORMANCE		n				111
Slew Rate	SR	$R_1 = 1 M\Omega, C_1 = 10 pF, A_V = 1$		60		V/ms
Settling Time to 0.1%	t _s	$V_{IN} = 1 \text{ V step}, R_I = 100 \text{ k}\Omega, C_I = 10 \text{ pF}$		13		μs
Gain Bandwidth Product	GBP	$R_{L} = 1 \text{ M}\Omega, C_{L} = 10 \text{ pF}, A_{V} = 1$		200		kHz
Phase Margin	Φ_{M}	$R_{L} = 1 \text{ M}\Omega, C_{L} = 10 \text{ pF}, A_{V} = 1$		60		Degrees
Channel Separation	CS	$f = 10 \text{ kHz}, R_i = 1 \text{ M}\Omega$		105		dB
EMI Rejection Ratio of +IN x	EMIRR	V _{IN} = 100 mV _{PEAK} , f = 400 MHz, 900 MHz, 1800 MHz, 2400 MHz		90		dB
NOISE PERFORMANCE						
Voltage Noise	e _n p-p	f = 0.1 Hz to 10 Hz		5		μV p-p
Voltage Noise Density	e _n	f = 1 kHz		50		nV/√Hz
3	"	f = 10 kHz		45		nV/√Hz
Current Noise Density	i _n	f = 1 kHz		0.1		pA/√Hz

ELECTRICAL CHARACTERISTICS—18 V OPERATION

 $V_{SY} = 18$ V, $V_{CM} = V_{SY}/2$, $T_A = 25$ °C, unless otherwise specified.

Table 4.

Parameter	Symbol	Test Conditions/Comments	Min	Тур	Max	Unit
INPUT CHARACTERISTICS					_	
Offset Voltage	Vos	$V_{CM} = 0 V \text{ to } 18 V$			350	μV
		$V_{CM} = 0.3 \text{ V to } 17.7 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +85^{\circ}\text{C}$			1.2	mV
		$V_{CM} = 0 \text{ V to } 18 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +85^{\circ}\text{C}$			4	mV
		$V_{CM} = 0.3 \text{ V to } 17.7 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$			2	mV
		$V_{CM} = 0 \text{ V to } 18 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$			11	mV
Input Bias Current	I _B			5	20	рА
		-40 °C \leq T _A \leq $+125$ °C			2.9	nA
Input Offset Current	I _{os}				40	рА
		$-40^{\circ}\text{C} \le \text{T}_{A} \le +125^{\circ}\text{C}$			500	pА
Input Voltage Range			0		18	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = 0 V \text{ to } 18 V$	95	110		dB
		$V_{CM} = 0.3 \text{ V to } 17.7 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +85^{\circ}\text{C}$	83			dB
		$V_{CM} = 0 \text{ V to } 18 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +85^{\circ}\text{C}$	74			dB
		$V_{CM} = 0.3 \text{ V to } 17.7 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$	80			dB
		$V_{CM} = 0 \text{ V to } 18 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$	67			dB
Large Signal Voltage Gain	A _{VO}	$R_L = 100 \text{ k}\Omega, V_O = 0.5 \text{ V to } 17.5 \text{ V}$	110	120		dB
		-40 °C \leq T _A \leq $+85$ °C	105			dB
		-40 °C $\leq T_A \leq +125$ °C	73			dB
Offset Voltage Drift	$\Delta V_{os}/\Delta T$			2		μV/°C
Input Resistance	R _{IN}			10		GΩ
Input Capacitance, Differential Mode	C _{INDM}			3.5		pF
Input Capacitance, Common Mode	C _{INCM}			10.5		pF
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$R_L = 100 \text{ k}\Omega \text{ to V}_{CM'} - 40^{\circ}\text{C} \le T_A \le +125^{\circ}\text{C}$	17.97			V
Output Voltage Low	V _{OL}	$R_L = 100 \text{ k}\Omega \text{ to } V_{CM'} - 40^{\circ}\text{C} \le T_A \le +125^{\circ}\text{C}$			30	mV
Short-Circuit Current	I _{sc}			±12		mA
Closed-Loop Output Impedance	Z _{out}	$f = 1 \text{ kHz, } A_V = 1$		15		Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_{SY} = 2.7 \text{ V to } 18 \text{ V}$	105	125		dB
		-40 °C $\leq T_A \leq +125$ °C	70			dB
Supply Current per Amplifier	I _{SY}	$I_0 = 0 \text{ mA}$		18	22	μΑ
		-40 °C \leq T _A \leq +125°C			33	μA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_1 = 1 M\Omega, C_1 = 10 pF, A_v = 1$		70		V/ms
Settling Time to 0.1%	t _s	$V_{IN} = 1 \text{ V step, } R_{I} = 100 \text{ k}\Omega, C_{I} = 10 \text{ pF}$		12		μs
Gain Bandwidth Product	GBP	$R_1 = 1 \text{ M}\Omega, C_1 = 10 \text{ pF}, A_v = 1$		200		kHz
Phase Margin	Φ_{M}	$R_1 = 1 \text{ M}\Omega, C_1 = 10 \text{ pF}, A_v = 1$		60		Degrees
Channel Separation	CS	$f = 10 \text{ kHz}, R_1 = 1 \text{ M}\Omega$		105		dB
EMI Rejection Ratio of +IN x	EMIRR	V _{IN} = 100 mV _{PEAK} , f = 400 MHz, 900 MHz, 1800 MHz, 2400 MHz		90		dB
NOISE PERFORMANCE		·				
Voltage Noise	e _n p-p	f = 0.1 Hz to 10 Hz		5		μV p-p
Voltage Noise Density	e _n	f = 1 kHz		50		nV/√Hz
3	"	f = 10 kHz		45		nV/√Hz
Current Noise Density	i _n	f = 1 kHz		0.1		pA/√Hz

ABSOLUTE MAXIMUM RATINGS

Table 4.

Parameter	Rating
Supply Voltage	20.5 V
Input Voltage	(V−) − 300 mV to (V+) + 300 mV
Input Current ¹	±10 mA
Differential Input Voltage	±V _{SY}
Output Short-Circuit	Indefinite
Duration to GND	
Temperature Range	
Storage	−65°C to +150°C
Operating	-40°C to +125°C
Junction	−65°C to +150°C
Lead Temperature	300°C
(Soldering, 60 sec)	

¹The input pins have clamp diodes to the power supply pins. Limit the input current to 10 mA or less whenever input signals exceed the power supply rail by 0.3 V.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL RESISTANCE

 θ_{JA} is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages using a standard 4-layer board.

Table 5. Thermal Resistance

Package Type	θ_{JA}	θ _{JC}	Unit
8-Lead MSOP (RM-8)	142	45	°C/W

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

TYPICAL PERFORMANCE CHARACTERISTICS

 $T_A = 25$ °C, unless otherwise noted.

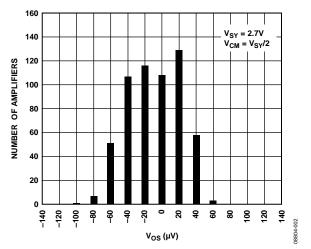


Figure 2. Input Offset Voltage Distribution

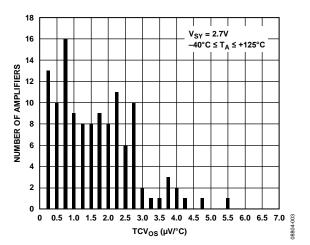


Figure 3. Input Offset Voltage Drift Distribution

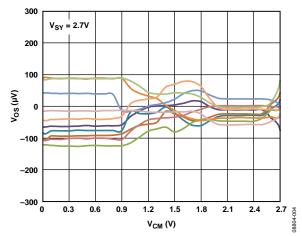


Figure 4. Input Offset Voltage vs. Common-Mode Voltage

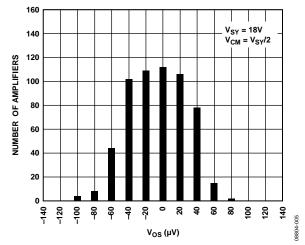


Figure 5. Input Offset Voltage Distribution

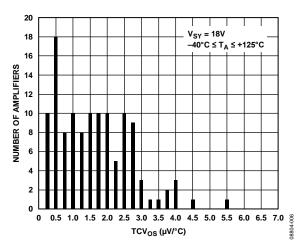


Figure 6. Input Offset Voltage Drift Distribution

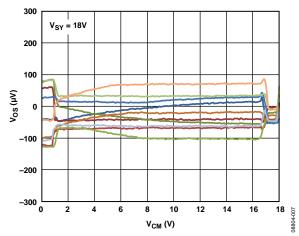


Figure 7. Input Offset Voltage vs. Common-Mode Voltage

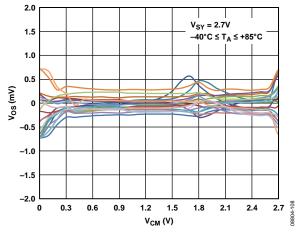


Figure 8. Input Offset Voltage vs. Common-Mode Voltage

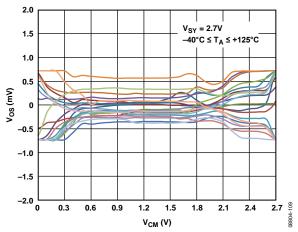


Figure 9. Input Offset Voltage vs. Common-Mode Voltage

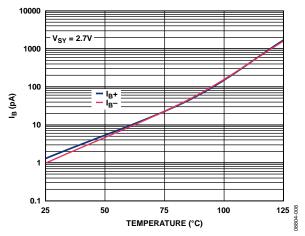


Figure 10. Input Bias Current vs. Temperature

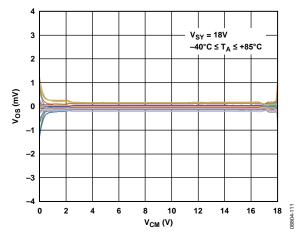


Figure 11. Input Offset Voltage vs. Common-Mode Voltage

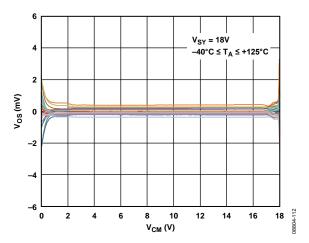


Figure 12. Input Offset Voltage vs. Common-Mode Voltage

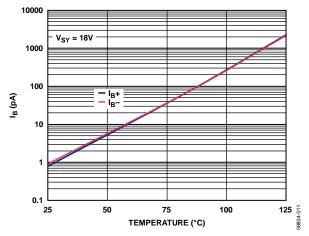


Figure 13. Input Bias Current vs. Temperature

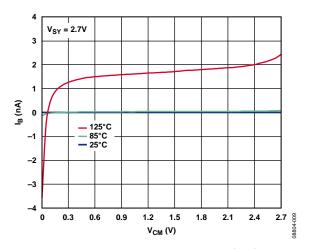


Figure 14. Input Bias Current vs. Common-Mode Voltage

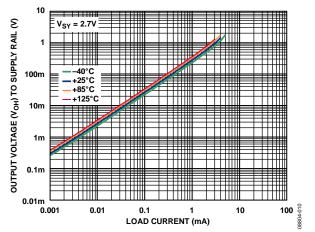


Figure 15. Output Voltage (V_{OH}) to Supply Rail vs. Load Current

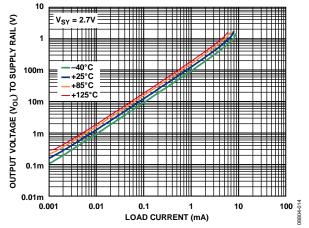


Figure 16. Output Voltage (V_{OL}) to Supply Rail vs. Load Current

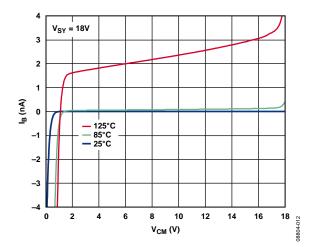


Figure 17. Input Bias Current vs. Common-Mode Voltage

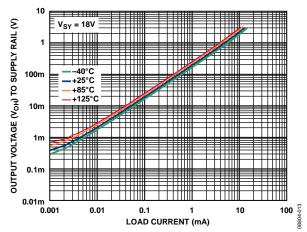


Figure 18. Output Voltage (V_{OH}) to Supply Rail vs. Load Current

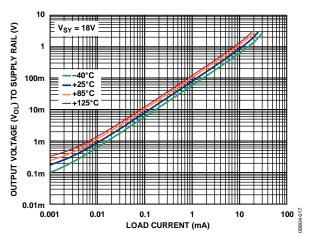


Figure 19. Output Voltage ($V_{\rm OL}$) to Supply Rail vs. Load Current

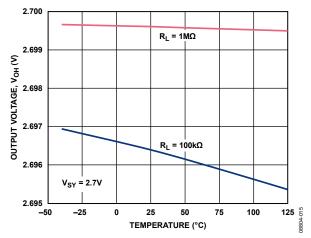


Figure 20. Output Voltage (V_{OH}) vs. Temperature

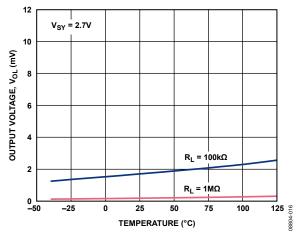


Figure 21. Output Voltage (Vol.) vs. Temperature

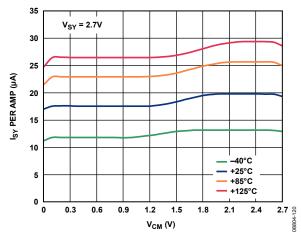


Figure 22. Supply Current per Amp vs. Common-Mode Voltage

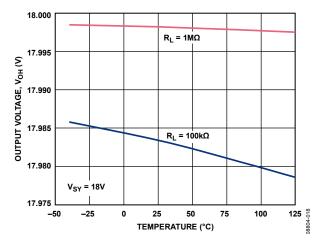


Figure 23. Output Voltage (V_{OH}) vs. Temperature

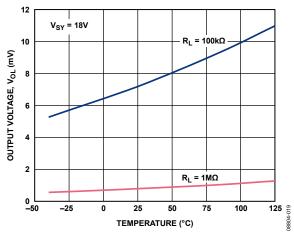


Figure 24. Output Voltage (V_{OL}) vs. Temperature

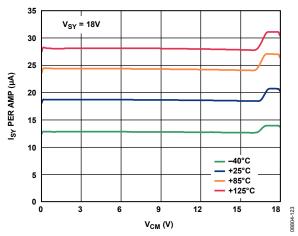


Figure 25. Supply Current per Amp vs. Common-Mode Voltage

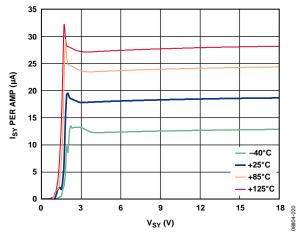


Figure 26. Supply Current per Amp vs. Supply Voltage

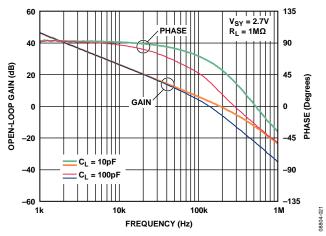


Figure 27. Open-Loop Gain and Phase vs. Frequency

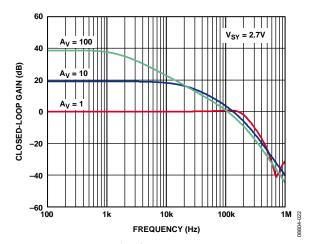


Figure 28. Closed-Loop Gain vs. Frequency

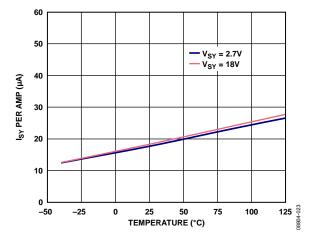


Figure 29. Supply Current per Amp vs. Temperature

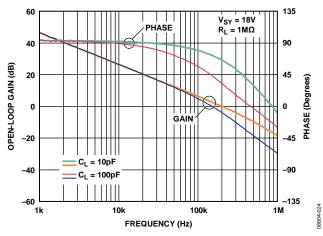


Figure 30. Open-Loop Gain and Phase vs. Frequency

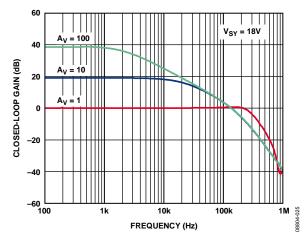


Figure 31. Closed-Loop Gain vs. Frequency

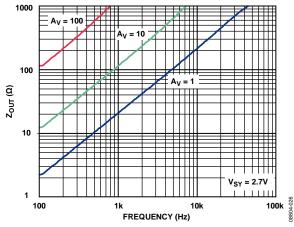


Figure 32. Output Impedance vs. Frequency

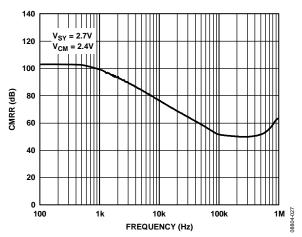


Figure 33. CMRR vs. Frequency

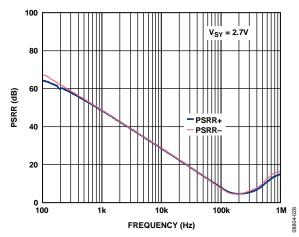


Figure 34. PSRR vs. Frequency

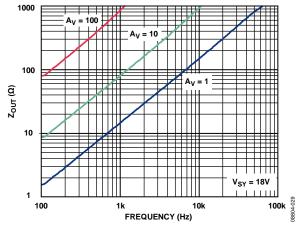


Figure 35. Output Impedance vs. Frequency

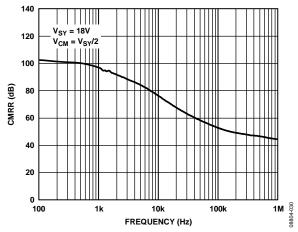


Figure 36. CMRR vs. Frequency

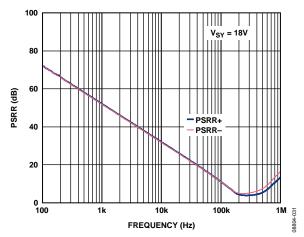


Figure 37. PSRR vs. Frequency

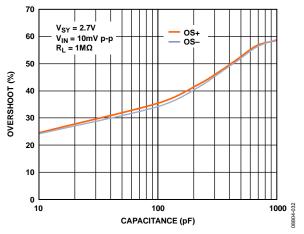


Figure 38. Small Signal Overshoot vs. Load Capacitance

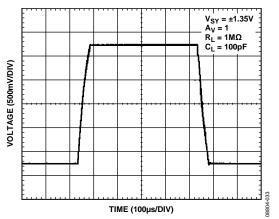


Figure 39. Large Signal Transient Response

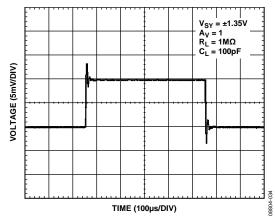


Figure 40. Small Signal Transient Response

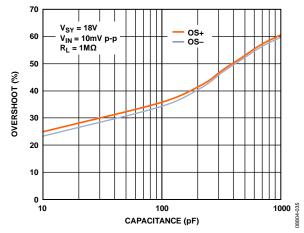


Figure 41. Small Signal Overshoot vs. Load Capacitance

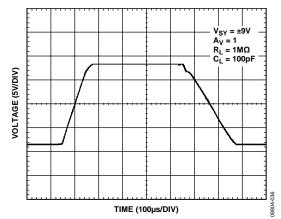


Figure 42. Large Signal Transient Response

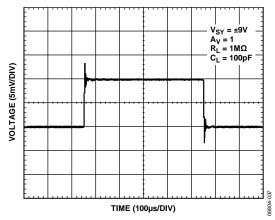


Figure 43. Small Signal Transient Response

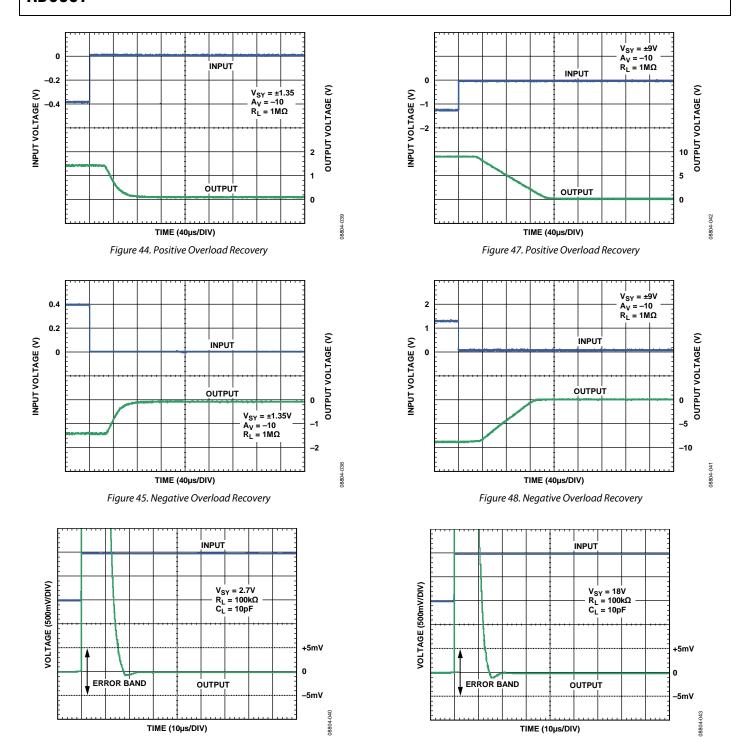


Figure 49. Positive Settling Time to 0.1%

Figure 46. Positive Settling Time to 0.1%

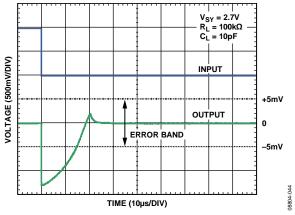


Figure 50. Negative Settling Time to 0.1%

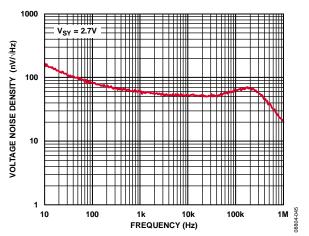


Figure 51. Voltage Noise Density vs. Frequency

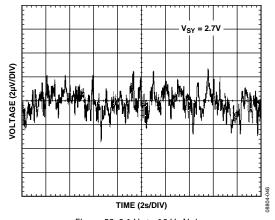


Figure 52. 0.1 Hz to 10 Hz Noise

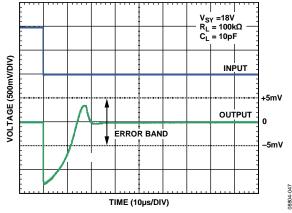


Figure 53. Negative Settling Time to 0.1%

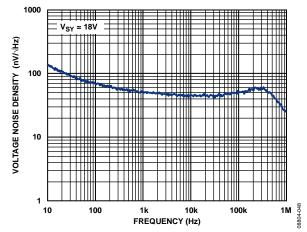


Figure 54. Voltage Noise Density vs. Frequency

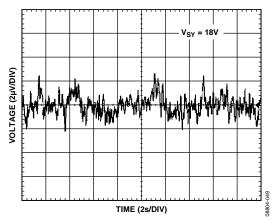


Figure 55. 0.1 Hz to 10 Hz Noise

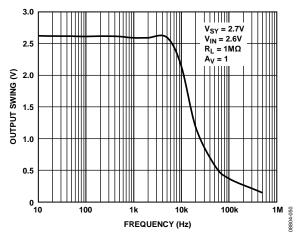


Figure 56. Output Swing vs. Frequency

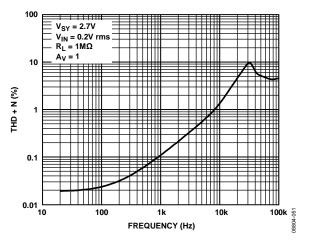


Figure 57. THD + N vs. Frequency

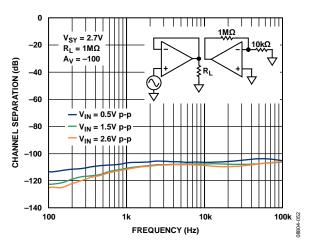


Figure 58. Channel Separation vs. Frequency

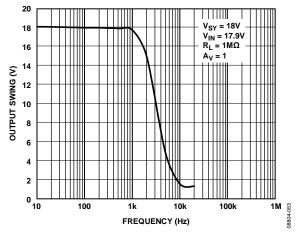


Figure 59. Output Swing vs. Frequency

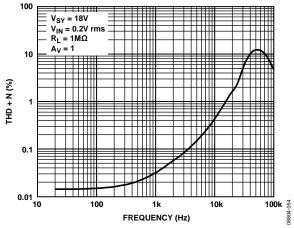


Figure 60. THD + N vs. Frequency

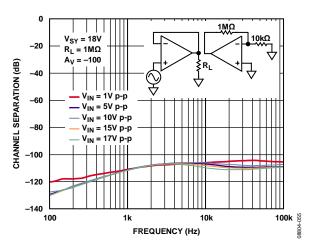


Figure 61. Channel Separation vs. Frequency

APPLICATIONS INFORMATION

The AD8657 is a low power, rail-to-rail input and output precision CMOS amplifier that operates over a wide supply voltage range of 2.7 V to 18 V. This amplifier uses the Analog Devices DigiTrim technique to achieve a higher degree of precision than is available from other CMOS amplifiers. The DigiTrim technique is a method of trimming the offset voltage of an amplifier after assembly. The advantage of postpackage trimming is that it corrects any shifts in offset voltage caused by mechanical stresses of assembly.

The AD8657 also employs unique input and output stages to achieve a rail-to-rail input and output range with a very low supply current.

INPUT STAGE

Figure 62 shows the simplified schematic of the AD8657. The input stage comprises two differential transistor pairs, an NMOS pair (M1, M2) and a PMOS pair (M3, M4). The input common-mode voltage determines which differential pair turns on and is more active than the other.

The PMOS differential pair is active when the input voltage approaches and reaches the lower supply rail. The NMOS pair is needed for input voltages up to and including the upper supply rail. This topology allows the amplifier to maintain a wide dynamic input voltage range and to maximize signal swing to both supply rails.

For the majority of the input common-mode voltage range, the PMOS differential pair is active. Differential pairs commonly exhibit different offset voltages. The handoff from one pair to the other creates a step-like characteristic that is visible in the $V_{\rm OS}$ vs. $V_{\rm CM}$ graph (see Figure 4 and Figure 7). This is inherent in all rail-to-rail amplifiers that use the dual differential pair topology. Therefore, always choose a common-mode voltage that does not include the region of handoff from one input differential pair to the other.

Additional steps in the $V_{\rm OS}$ vs. $V_{\rm CM}$ curves are also visible as the input common-mode voltage approaches the power supply rails. These changes are a result of the load transistors (M8, M9, M14, and M15) running out of headroom. As the load transistors are forced into the triode region of operation, the mismatch of their drain impedances contributes to the offset voltage of the amplifier. This problem is exacerbated at high temperatures due to the decrease in the threshold voltage of the input transistors (see

Figure 8, Figure 9, Figure 11, and Figure 12 for typical performance data).

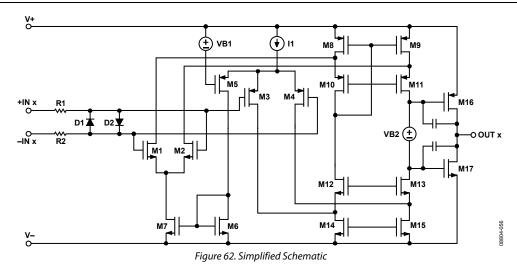
Current Source I1 drives the PMOS transistor pair. As the input common-mode voltage approaches the upper rail, I1 is steered away from the PMOS differential pair through the M5 transistor. The bias voltage, VB1, controls the point where this transfer occurs. M5 diverts the tail current into a current mirror consisting of the M6 and M7 transistors. The output of the current mirror then drives the NMOS pair. Note that the activation of this current mirror causes a slight increase in supply current at high commonmode voltages (see Figure 22 and Figure 25 for more details).

The AD8657 achieves its high performance by using low voltage MOS devices for its differential inputs. These low voltage MOS devices offer excellent noise and bandwidth per unit of current. Each differential input pair is protected by proprietary regulation circuitry (not shown in the simplified schematic). The regulation circuitry consists of a combination of active devices that maintain the proper voltages across the input pairs during normal operation and passive clamping devices that protect the amplifier during fast transients. However, these passive clamping devices begin to forward bias as the common-mode voltage approaches either power supply rail. This causes an increase in the input bias current (see Figure 14 and Figure 17).

The input devices are also protected from large differential input voltages by clamp diodes (D1 and D2). These diodes are buffered from the inputs with two 10 k Ω resistors (R1 and R2). The differential diodes turn on whenever the differential voltage exceeds approximately 600 mV; in this condition, the differential input resistance drops to 20 k Ω .

OUTPUT STAGE

The AD8657 features a complementary output stage consisting of the M16 and M17 transistors. These transistors are configured in Class AB topology and are biased by the voltage source, VB2. This topology allows the output voltage to approach, within millivolts, the supply rails, achieving a rail-to-rail output swing. The output voltage is limited by the output impedance of the transistors, which are low $R_{\rm ON}$ MOS devices. The output voltage swing is a function of the load current and can be estimated using the output voltage to the supply rail vs. load current plots (see Figure 15, Figure 16, Figure 18, and Figure 19).



RAIL TO RAIL

The AD8657 features rail-to-rail input and output with a supply voltage from 2.7 V to 18 V. Figure 63 shows the input and output waveforms of the AD8657 configured as a unity-gain buffer with a supply voltage of ± 9 V and a resistive load of 1 M Ω . With an input voltage of ± 9 V, the AD8657 allows the output to swing very close to both rails. Additionally, it does not exhibit phase reversal.

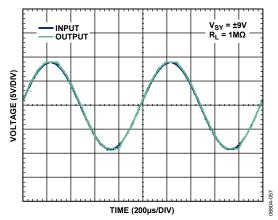


Figure 63. Rail-to-Rail Input and Output

RESISTIVE LOAD

The feedback resistor alters the load resistance that an amplifier sees. It is, therefore, important to be aware of the value of feedback resistors chosen for use with the AD8657. The AD8657 is capable of driving resistive loads down to $100\ k\Omega.$ The following two examples, inverting and noninverting configurations, show how the feedback resistor changes the actual load resistance seen at the output of the amplifier.

Inverting Configuration

Figure 64 shows AD8657 in an inverting configuration with a resistive load, R_L , at the output. The actual load seen by the amplifier is the parallel combination of the feedback resistor, R2, and load, R_L . Having a feedback resistor of 1 $k\Omega$ and a load of 1 $M\Omega$ results in an equivalent load resistance of 999 Ω at the output. In this condition, the AD8657 is incapable of driving such a heavy load; therefore, its performance degrades greatly. To avoid loading the output, use a larger feedback resistor, but consider the resistor thermal noise effect on the overall circuit.

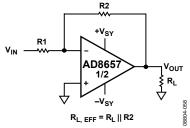


Figure 64. Inverting Op Amp

Noninverting Configuration

Figure 65 shows the AD8657 in a noninverting configuration with a resistive load, R_L , at the output. The actual load seen by the amplifier is the parallel combination of R1 + R2 and R_L .

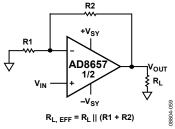


Figure 65. Noninverting Op Amp

COMPARATOR OPERATION

Op amps are designed to operate in a closed-loop configuration with feedback from its output to its inverting input. Figure 66 shows the AD8657 configured as a voltage follower with an input voltage that is always kept at midpoint of the power supplies. The same configuration is applied to the unused channel. A1 and A2 indicate the placement of ammeters to measure supply current. $I_{\rm SY}+$ refers to the current flowing from the upper supply rail to the op amp, and $I_{\rm SY}-$ refers to the current flowing from the op amp to the lower supply rail. As shown in Figure 67, as expected, in normal operating condition, the total current flowing into the op amp is equivalent to the total current flowing out of the op amp, where, $I_{\rm SY}+=I_{\rm SY}-=36~\mu{\rm A}$ for the dual AD8657 at $V_{\rm SY}=18~\rm V$.

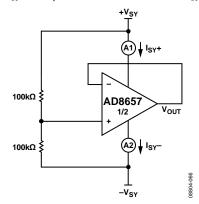


Figure 66. Voltage Follower

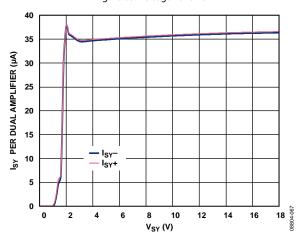


Figure 67. Supply Current vs. Supply Voltage (Voltage Follower)

In contrast to op amps, comparators are designed to work in an open-loop configuration and to drive logic circuits. Although op amps are different from comparators, occasionally an unused section of a dual op amp is used as a comparator to save board space and cost; however, this is not recommended.

Figure 68 and Figure 69 show the AD8657 configured as a comparator, with 100 k Ω resistors in series with the input pins. Any unused channels are configured as buffers with the input voltage kept at the midpoint of the power supplies. The AD8657 has input devices that are protected from large differential input voltages by Diode D1 and Diode D2 (refer to Figure 62). These diodes

consist of substrate PNP bipolar transistors, and conduct whenever the differential input voltage exceeds approximately 600 mV; however, these diodes also allow a current path from the input to the lower supply rail, thus resulting in an increase in the total supply current of the system. As shown in Figure 70, both configurations yield the same result. At 18 V of power supply, $I_{\rm SY}+$ remains at 36 μA per dual amplifier, but $I_{\rm SY}-$ increases to 140 μA in magnitude per dual amplifier.

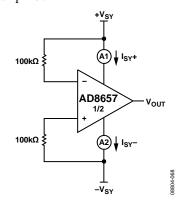


Figure 68. Comparator A

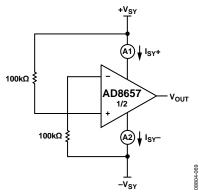


Figure 69. Comparator B

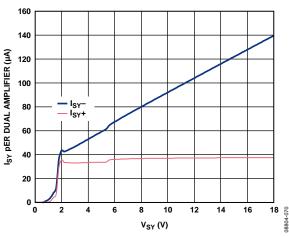


Figure 70. Supply Current vs. Supply Voltage (AD8657 as a Comparator)

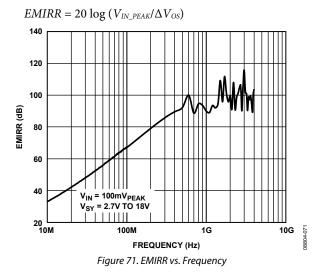
Note that $100 \text{ k}\Omega$ resistors are used in series with the input of the op amp. If smaller resistor values are used, the supply current of the system increases much more. For more details on op amps as comparators, refer to the AN-849 Application Note *Using Op Amps as Comparators*.

EMI REJECTION RATIO

Circuit performance is often adversely affected by high frequency electromagnetic interference (EMI). In the event where signal strength is low and transmission lines are long, an op amp must accurately amplify the input signals. However, all op amp pins—the noninverting input, inverting input, positive supply, negative supply, and output pins—are susceptible to EMI signals. These high frequency signals are coupled into an op amp by various means such as conduction, near field radiation, or far field radiation. For instance, wires and PCB traces can act as antennas and pick up high frequency EMI signals.

Precision op amps, such as the AD8657, do not amplify EMI or RF signals because of their relatively low bandwidth. However, due to the nonlinearities of the input devices, op amps can rectify these out-of-band signals. When these high frequency signals are rectified, they appear as a dc offset at the output.

To describe the ability of the AD8657 to perform as intended in the presence of an electromagnetic energy, the electromagnetic interference rejection ratio (EMIRR) of the noninverting pin is specified in Table 2, Table 3, and Table 4 of the Specifications section. A mathematical method of measuring EMIRR is defined as follows:



4 mA TO 20 mA PROCESS CONTROL CURRENT LOOP TRANSMITTER

The 2-wire current transmitters are often used in distributed control systems and process control applications to transmit analog signals between sensors and process controllers. Figure 72 shows a 4 mA to 20 mA current loop transmitter.

The transmitter powers directly from the control loop power supply, and the current in the loop carries signal from 4 mA to 20 mA. Thus, 4 mA establishes the baseline current budget within which the circuit must operate. Using the AD8657 is an excellent

choice due to its low supply current of 33 μA per amplifier over temperature and supply voltage. The current transmitter controls the current flowing in the loop, where a zero-scale input signal is represented by 4 mA of current and a full-scale input signal is represented by 20 mA. The transmitter also floats from the control loop power supply, V_{DD} , while signal ground is in the receiver. The loop current is measured at the load resistor, R_L , at the receiver side.

With a zero-scale input, a current of $V_{\text{REF}}/R_{\text{NULL}}$ flows through R´. This creates a current flowing through the sense resistor, I_{SENSE} , determined by the following equation (see Figure 72 for details):

$$I_{SENSE, MIN} = (V_{REF} \times R')/(R_{NULL} \times R_{SENSE})$$

With a full-scale input voltage, current flowing through R´ is increased by the full-scale change in $V_{\rm IN}/R_{\rm SPAN}$. This creates an increase in the current flowing through the sense resistor.

 $I_{SENSE, DELTA} = (Full-Scale Change in V_{IN} \times R')/(R_{SPAN} \times R_{SENSE})$

Therefore

 $I_{SENSE, MAX} = I_{SENSE, MIN} + I_{SENSE, DELTA}$

When $R' >> R_{SENSE}$, the current through the load resistor at the receiver side is almost equivalent to I_{SENSE} .

Figure 72 is designed for a full-scale input voltage of 5 V. At 0 V of input, loop current is 3.5 mA, and at a full scale of 5 V, the loop current is 21 mA. This allows software calibration to fine tune the current loop to the 4 mA to 20 mA range.

The AD8657 and ADR125 both consume only 160 μ A quiescent current, making 3.34 mA current available to power additional signal conditioning circuitry or to power a bridge circuit.

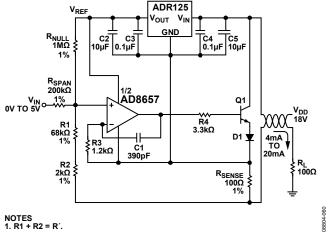


Figure 72. 4 mA to 20 mA Current Loop Transmitter

OUTLINE DIMENSIONS

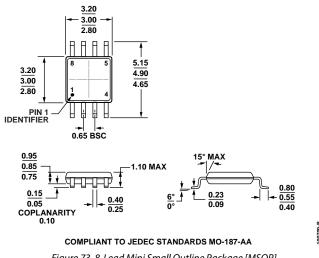


Figure 73. 8-Lead Mini Small Outline Package [MSOP] (RM-8) Dimensions shown in millimeters

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option	Branding
AD8657ARMZ	-40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	A2N
AD8657ARMZ-R7	-40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	A2N
AD8657ARMZ-RL	-40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	A2N

 $^{^{1}}$ Z = RoHS Compliant Part.

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